Fast turn-off Thyristor
P0295WC12#

The data sheet on the subsequent pages of this document is a scanned copy of existing data for this product.
(Rating Report 83TR5 Issue 2)

This data reflects the old part number for this product which is: P200CH02-12. This part number must **NOT** be used for ordering purposes – please use the ordering particulars detailed below.

The limitations of this data are as follows:
Device only available for grade 12 (1200V V_{RRM}/V_{DRM})

Please use the following link to view an up to date outline drawing for this device
Outline W8

Where any information on the product matrix page differs from that in the following data, the product matrix must be considered correct

An electronic data sheet for this product is presently in preparation.

For further information on this product, please contact your local ASM or distributor.

Alternatively, please contact Westcode as detailed below.

Ordering Particulars			
P0295	WC	♦♦	#
Fixed Type Code	Fixed Outline Code	Voltage code $V_{DRM}/100$ 12	Fixed Turn-off Time Code D = 20µs, E = 25µs, F = 30µs
Typical Order Code: P0295WC12D, 14.4mm clamp height, 1200V V_{RRM}/V_{DRM}, 20µs t_q			

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QUALITY EVALUATION LABORATORY

Rating Report: 83TR 5 (Issue 2) Date: 29th January, 1985

Origin: Pages: 24

Capsule Thyristor Type P200CH02-H12

Written: B.W.P. Brown Checked: BWPB Approved: BWPB

The P200CH02-H12 series of thyristors are centre regenerative gate diffused devices in cold weld capsules, a 24 mm slice is employed.

Ratings and Characteristics

Ratings

Voltage Grades	: H02-H12
V_{DSM}	: 200-1200V
V_{RSM}	: 300-1300V
V_{DRM}, V_{RRM}	: 200-1200V

$I_{T(AV)}$; Single phase; 50Hz, 180° sinewave Double side cooled, T_{HS} = 55°C; 85°C	: 295A, 195A
Single side cooled, T_{HS} = 85°C	: 110A
I_T(rms) Double side cooled, T_{HS} = 25°C	: 600A
I_T d.c. " " " T_{HS} = 25°C	: 480A
I_{TSM} : t = 10ms half sinewave; T_J (initial) = 125°C; V_{RM} = 0.6V_{RRM}(MAX)	: 2700A
I_{TSM} : t = 10ms half sinewave; T_J (initial) = 125°C; $V_{RM} \leqslant$ 10V	: 2970A
I^2t : t = 10ms; T_J (initial) = 125°C; V_{RM} = 0.6V_{RRM}(MAX)	: 36.5 x $10^3 A^2$SEC
I^2t : t = 10ms; T_J (initial) = 125°C; $V_{RM} \leqslant$ 10V	: 44.1 x $10^3 A^2$SEC
I^2t : t = 3ms; T_J (initial) = 125°C; $V_{RM} \leqslant$ 10V	: 32.4 x $10^3 A^2$SEC
di/dt : (Repetitive): T_J 125°C Gate: 20V. 20Ω Rise time 1uS	: 500A/uS
I_{FGM} : Anode positive with respect to cathode	: 18A
V_{FGM} : " " " " " "	: 12V
V_{RGM} :	: 5V
$P_{G(AV)}$:	: 1.5W
P_{GM} :	: 60W
V_{GD} :	: 0.25V
T_{HS} operating range	: -40°C to 125°C
T_{stg} Non-operating	: -40°C to 150°C

Characteristics

(maximum values unless stated otherwise)

I_{GT} : T_J = 25°C)		
I_H : T_J = 25°C)	V_A = 6 V : I_A = 1 A	
V_{GT} : T_J = 25°C)		
V_{GT} : T_J = 25°C		: 200mA
I_H : T_J = 25°C		: 600mA
V_{GT} : T_J = 25°C		: 3V
V_O : T_J = 125°C		: 1.6V
r_T : T_J = 125°C		: 1.23mohms
V_{TM} : I_{TM} = 715A	T_{VJ} = 125°C	: 2.48V
R_{th}(J-HS) Double side cooled		: 0.095°C/W
Single side cooled		: 0.19°C/W
dV/dt : Linear ramp to 0.8$V_{DRM(max)}$	T_J = 125°C: Gate O/C	repetitive : 200V/us*
I_{DRM} : T_J = 125°C :	V_{DM} = $V_{DRM(max)}$	: 30mA
I_{RRM} : T_J = 125°C :	V_{RM} = $V_{RRM(max)}$	: 30mA
Q_{RR} : I_{TM} = 300A : dI/dt :20 A/us, 50% chord value		
V_{RM} : 50V	T_{VJ} = 125°C	: 25uC (Typical)
tq : I_{TM} = 300A; dI/dt :20 A/us :	T_J = 125°C V_{RM} = 50V	
dV/dt = 200V/us to 0.8V_{DRM}		: 25 -40uS
When specified 20V/us to 0.8V_{DRM}		: 20 -35uS(Typica
Mounting force:		: 330-550Kgf
Outline drawing:		: 101A212
Outline (JEDEC NO.)		: TO-200AB

Extension of Turn-off Time

This Report is applicable to other tq/reapplied dv/dt combinations when supply has been agreed by Sales/Production.

* Repetitive dv/dt

Higher dv/dt selections are available up to 1000V/us on request.

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Voltage Ratings

Voltage Grade 'H'	V_{DSM} V_{DRM} V_{RRM} V	V_{RSM} V	V_D V_R DC
02	200	300	140
03	300	400	210
04	400	500	260
06	600	700	420
08	800	900	560
10	1000	1100	700
12	1200	1300	810

Extension of Voltage Grades

This report is applicable to other and higher voltage grades when supply has been agreed by Sales/Production.

2. INTRODUCTION

The P200CH02-H12 thyristor series are diffused regenerative gate devices employing a 24 mm slice in cold weld housings.

3. NOTES ON THE RATINGS

a) Rate of rise of on-state current

The maximum un-primed rate of rise of on-state current must not exceed 1000A/uS at any time during turn-on on a non-repetitive basis. For repetitive performance the on-state rate of rise of current must not exceed 500A/uS at any time during turn-on. Note that these values of current rate of rise apply to the circuit external to the device and its specified snubber network and device current rates of rise will be higher.

b) Square wave ratings

These ratings are given for leading edge linear rates of rise of forward current of 100 and 500 A/uS.

c) Duty Cycle Lines

The 100% duty cycle line appears on all these ratings. These frequency ratings are presented in the form that all duty cycles may be represented by straight parallel lines.

d) Maximum operating frequency

The maximum operating frequency is set by the time required for the thyristor to turn off (tq) and for the off-state voltage to reach full value (tv), i.e.

$$f_{max.} = \frac{1}{t_{pulse} + tq + tv}$$

e) Energy per pulse characteristics

These curves enable rapid estimation of device dissipation to be obtained for conditions not covered by the frequency ratings.

Let Ep be the Energy per pulse for a given current and pulse width, in joules

Let R_{th} be the steady-state thermal resistance (junction to sink)

and T_{SINK} be the heat sink temperature

Then the average dissipation will be

$$W_{AV} = Ep \times f$$

and

$$T_{SINK} = 125 - W_{AV}. R_{th}$$

4. REVERSE RECOVERY LOSS

On account of the number of circuit variables affecting reverse recovery voltage, no allowance for reverse recovery loss has been made in these ratings. The following procedure is recommended for use where it is necessary to include reverse recovery loss.

a) Determination by Measurement

From waveforms of recovery current obtained from a high frequency shunt (see Note 1) and reverse voltage present during recovery, an instantaneous reverse recovery loss waveform must be constructed. Let the area under this waveform be A joules per pulse. A new heat sink temperature can then be evaluated from:

$$T_{SINK\ (new)} = T_{SINK\ (original)} - A \left(\frac{r_t . 10^6}{t} + R_{th} \times f \right)$$

where $r_t = 1.64 \times 10^{-4} \sqrt{t}$

t = duration of reverse recovery loss per pulse in microseconds

A = Area under reverse loss waveform per pulse in joules (W.S.)

f = rated frequency at the original heat sink temperature

The total dissipation is now given by

$$W_{(TOT)} = W_{(original)} + A \times f$$

b) Determination without Measurement

In circumstances where it is not possible to measure voltage and current conditions, or for design purposes, the additional losses may be estimated from curves on page 14. A typical R-C snubber network is connected across the thyristor to control the transient reverse voltage waveform.

Let E be the value of energy per reverse cycle in joules (curves on p. 14)

Let f be the operating frequency in Hz

then $T_{SINK\ new} = T_{SINK\ original} - (E \times R_{th} \times f)$

where $T_{SINK\ new}$ is the required maximum heat sink temperature

and T_{SINK} original is the heat sink temperature given with the frequency ratings.

5. GATE DRIVE

The recommended gate drive is 20V, 20ohms with a short-circuit current rise time of not more than 1us. This gate drive must be applied when using the full di/dt capability of the device.

6. THE DV/DT SUPPRESSION NETWORK

The effect of a conventional resistor-capacitor snubber of 0.22 uF 22 ohms has been included in these ratings and all rating di/dt values apply to the circuit external to the thyristor and its suppression network.

7. NOTE 1

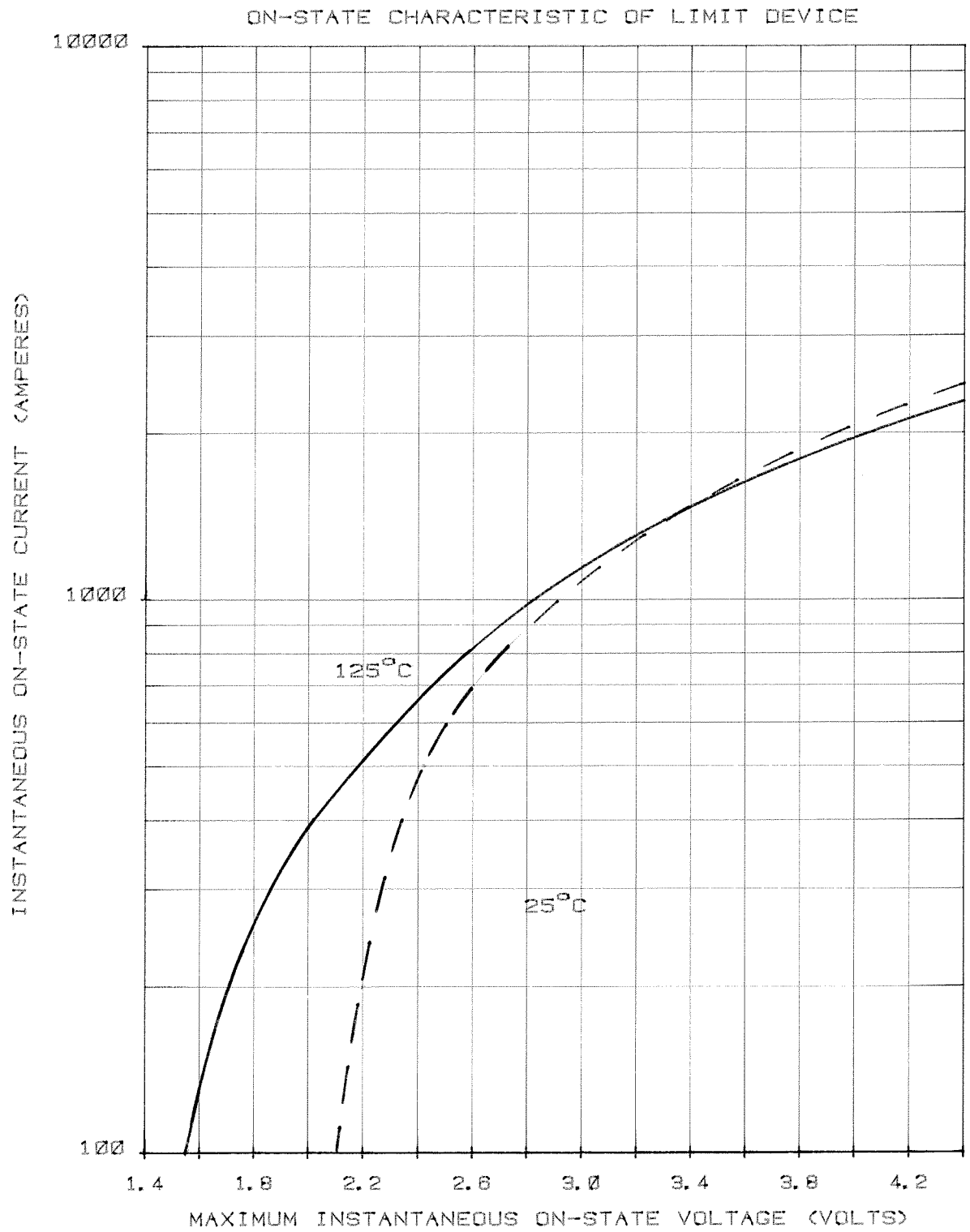
REVERSE RECOVERY LOSS BY MEASUREMENT

This thyristor has a low reverse recovered charge and peak reverse recovery current. When measuring the charge care must be taken to ensure that:

a) a.c. coupled devices such as current transformers are not affected by prior passage of high amplitude forward current.

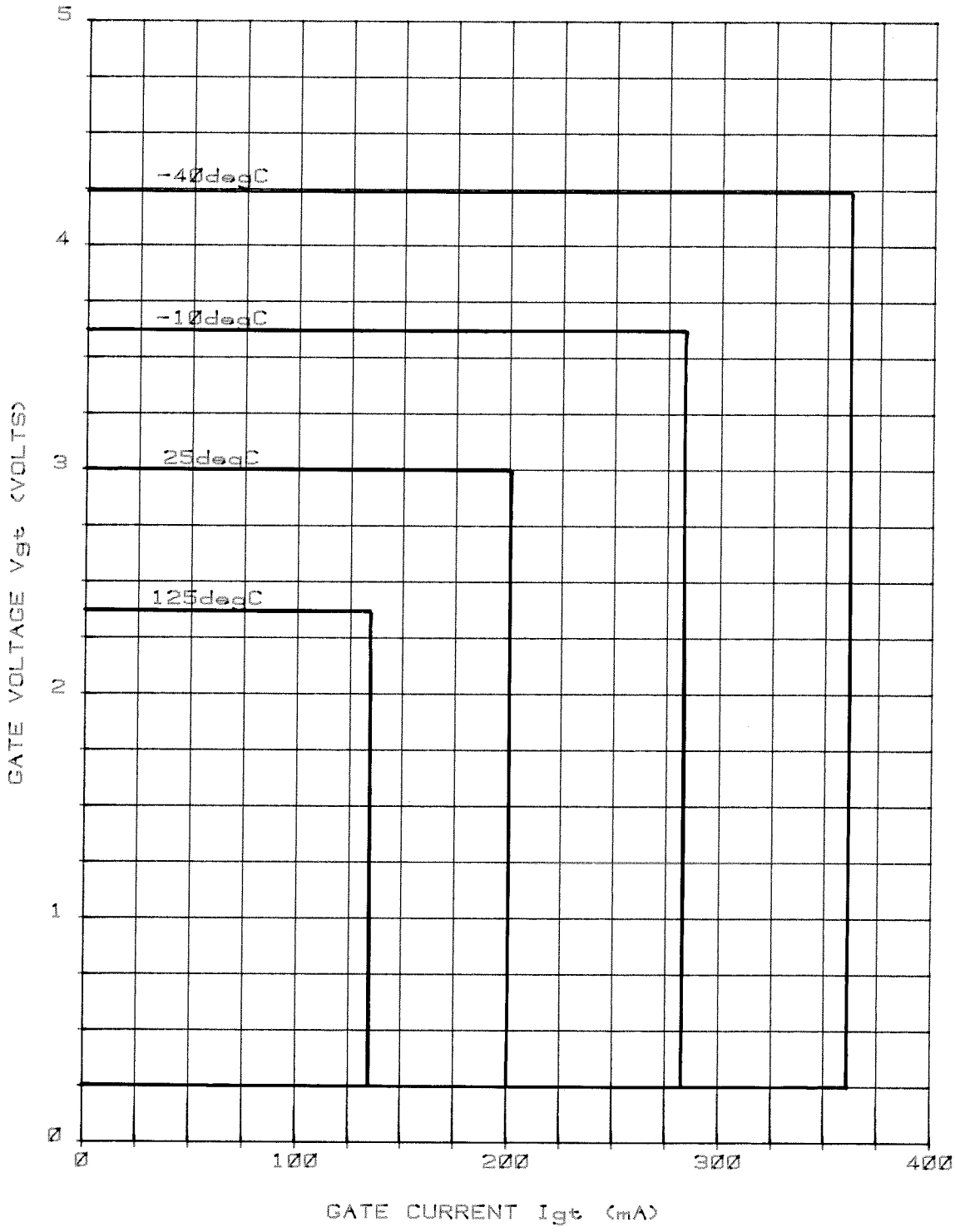
b) The measuring oscilloscope has adequate dynamic range - typically 100 screen heights - to cope with the initial forward current without overload.

P900C 116

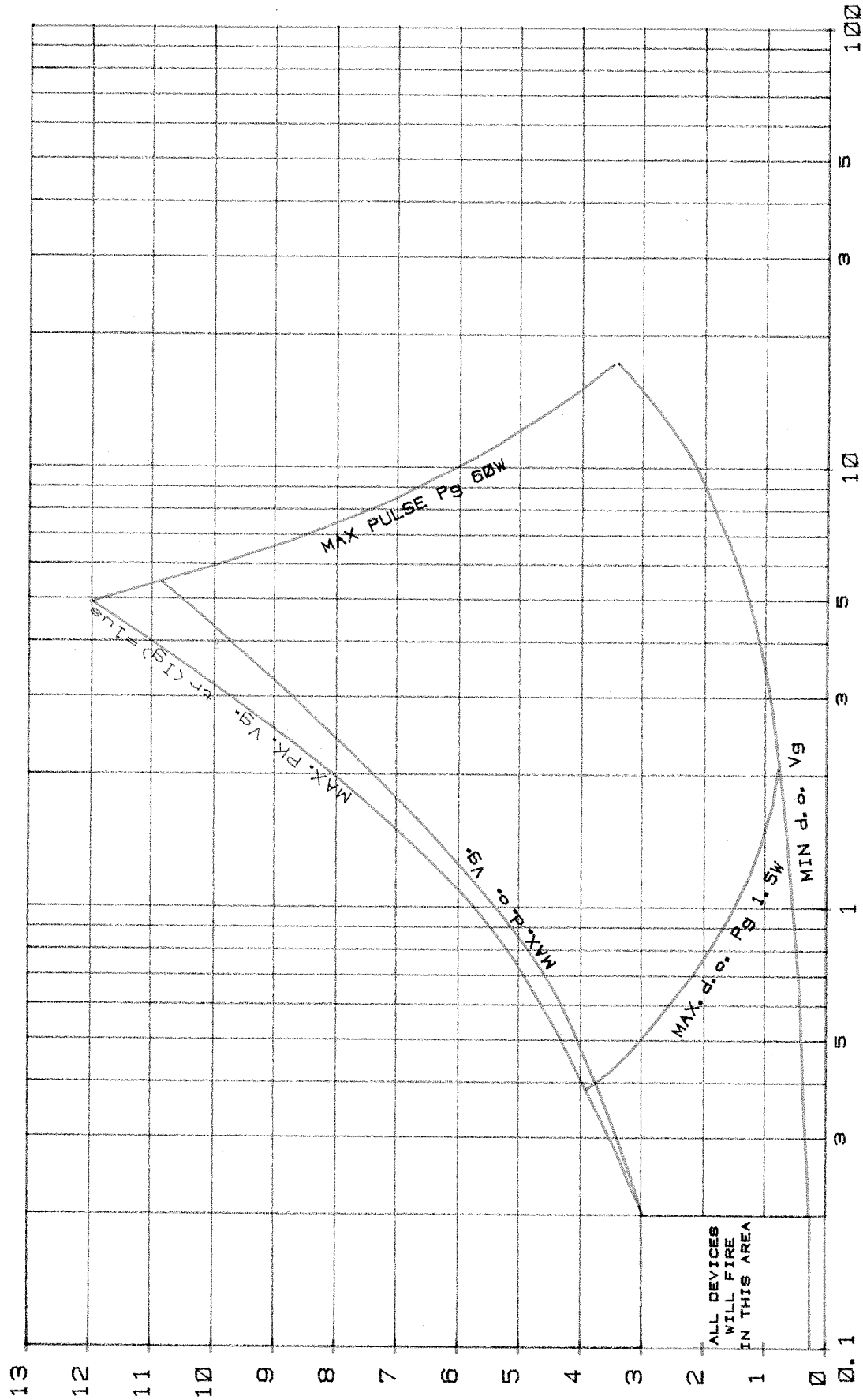

ON-STATE CHARACTERISTIC OF LIMIT DEVICE
10000
1000
100
INSTANTANEOUS ON-STATE CURRENT (AMPERES)
125°C
25°C
1.4
1.8
2.2
2.6
3.0
3.4
3.8
4.2
MAXIMUM INSTANTANEOUS ON-STATE VOLTAGE (VOLTS)

GATE TRIGGERING CHARACTERISTICS

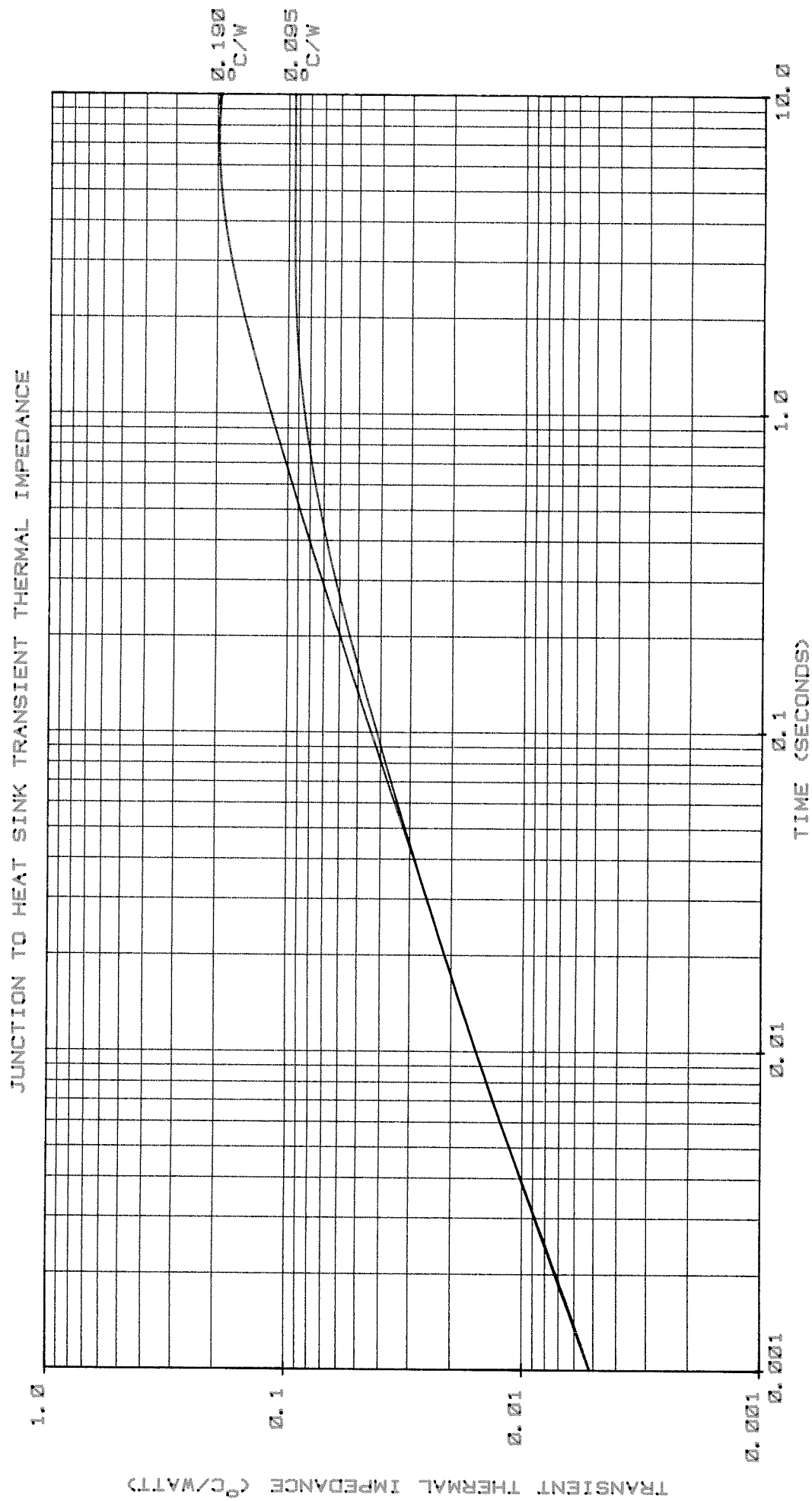
(TRIGGER POINTS OF ALL THYRISTORS LIE IN THE AREAS SHOWN)



GATE CHARACTERISTICS AT 25°C JUNCTION TEMPERATURE



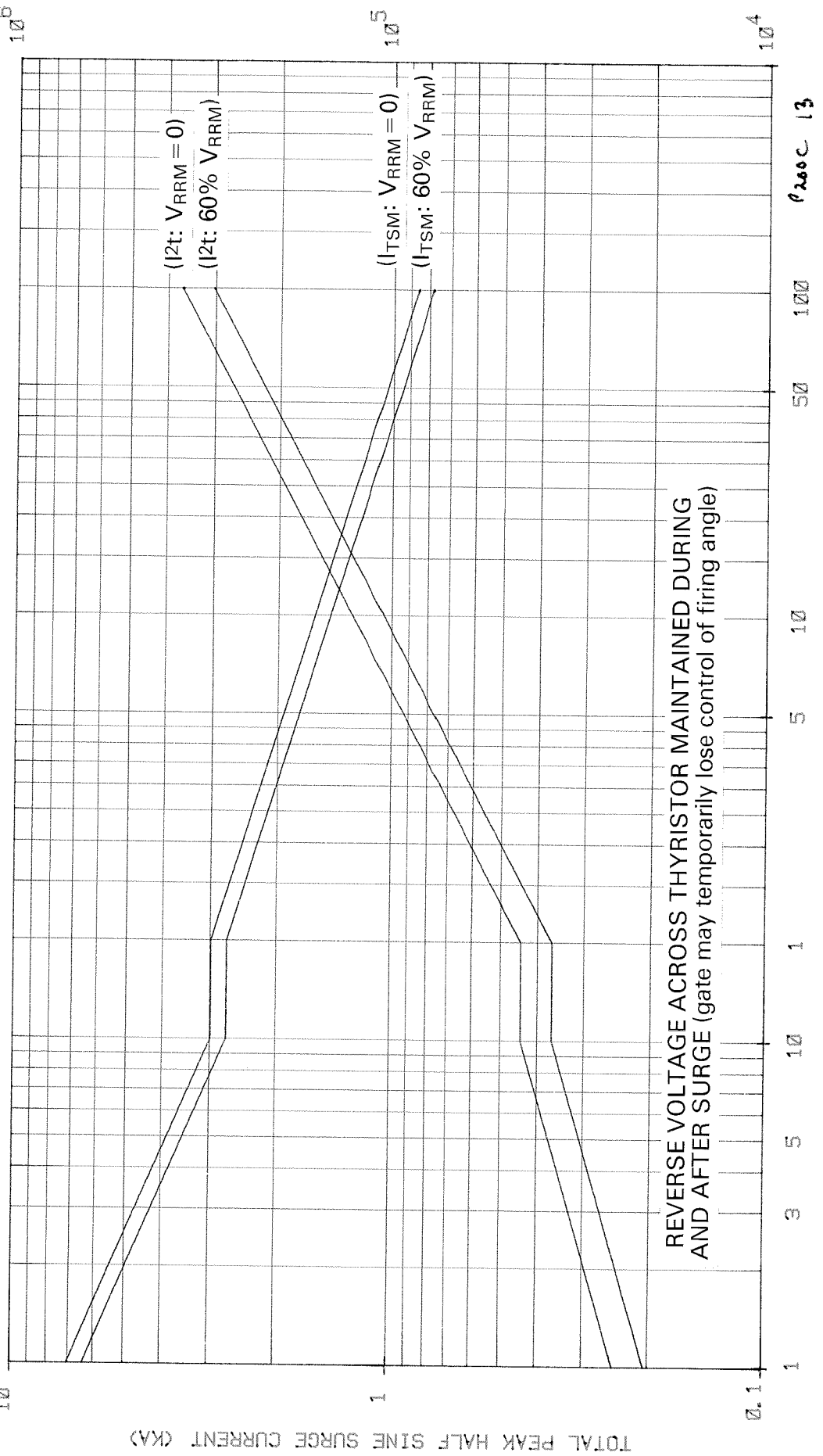
P200C / 12


JUNCTION TO HEAT SINK TRANSIENT THERMAL IMPEDANCE
0.190 °C/W
0.095 °C/W
TRANSIENT THERMAL IMPEDANCE (°C/WATT)
1.0
0.1
0.01
0.001
0.001
0.01
0.1
1.0
10.0
TIME (SECONDS)

P200C 13

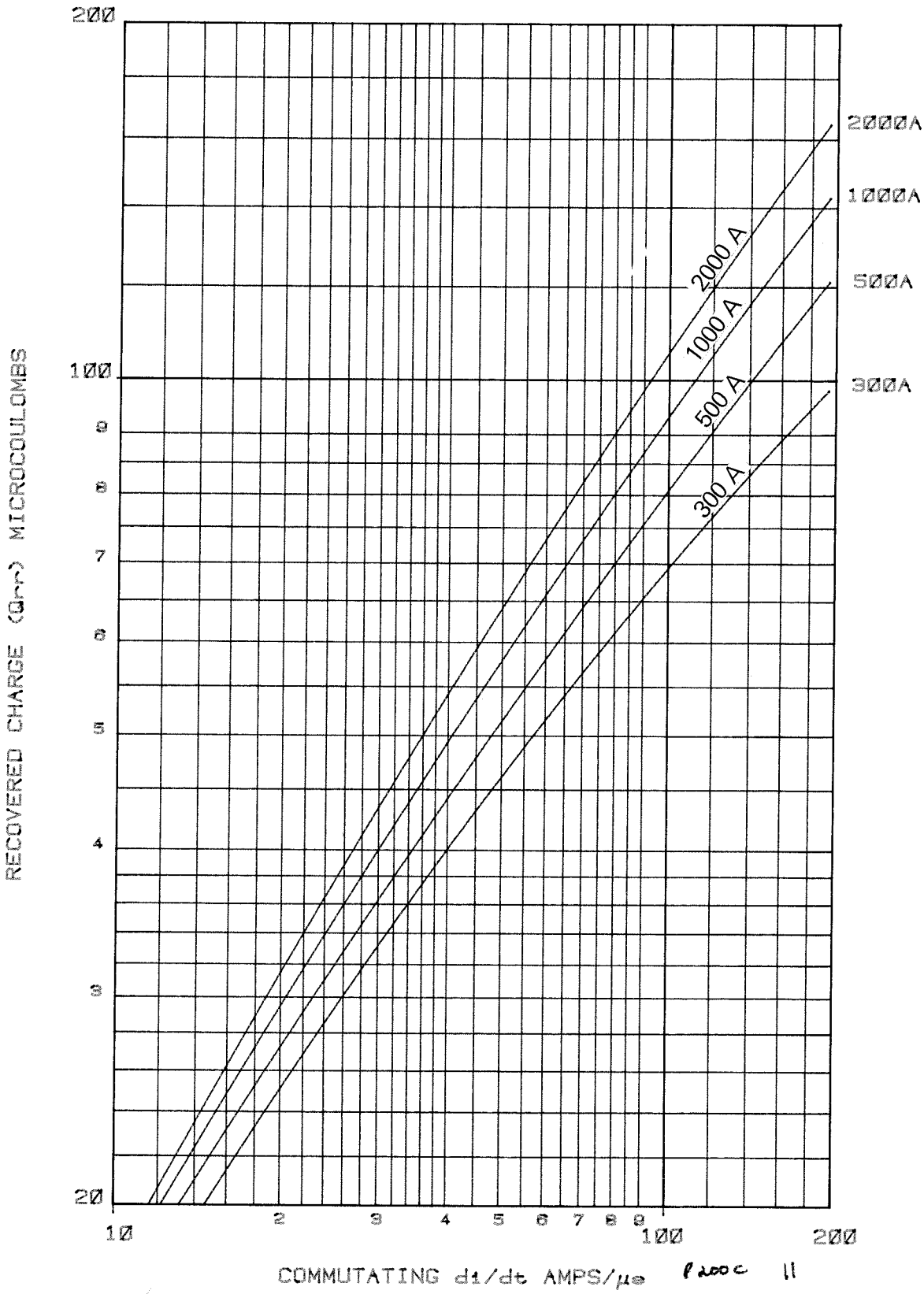
MAXIMUM NON REPETITIVE SURGE CURRENT AT INITIAL JUNCTION TEMPERATURE 125°C

GATE MAY TEMPORARILY LOSE CONTROL OF CONDUCTION ANGLE)



P200C/11

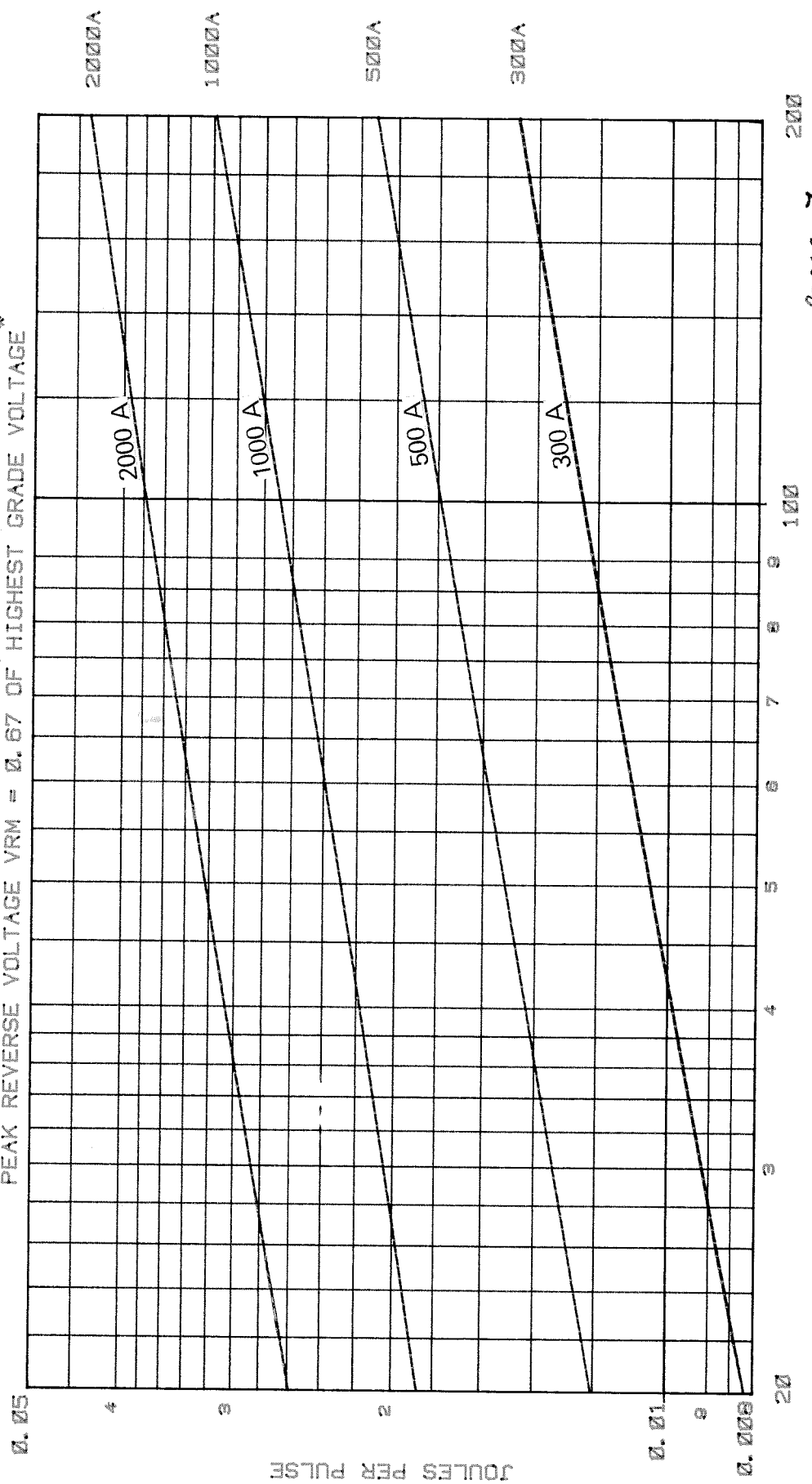
TYPICAL RECOVERED CHARGE AT 125°C JUNCTION TEMPERATURE



P200C 17

MAXIMUM REVERSE RECOVERY ENERGY LOSS PER PULSE, 125°C JUNCTION TEMPERATURE

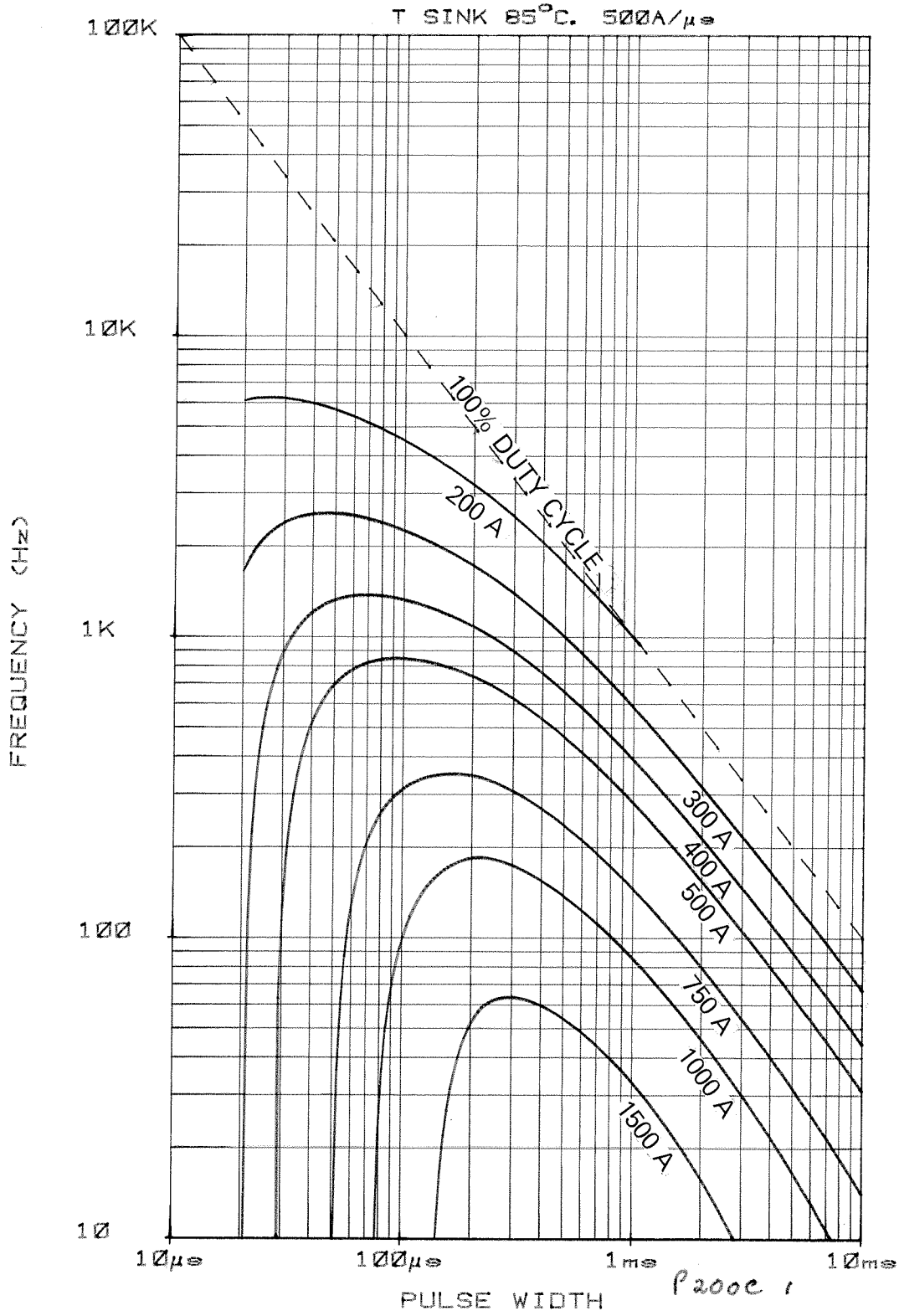
SNUBBER CONNECTED Ø.22μF, 22 OHMS
PEAK REVERSE VOLTAGE VRM = Ø.67 OF HIGHEST GRADE VOLTAGE*



P200C 7

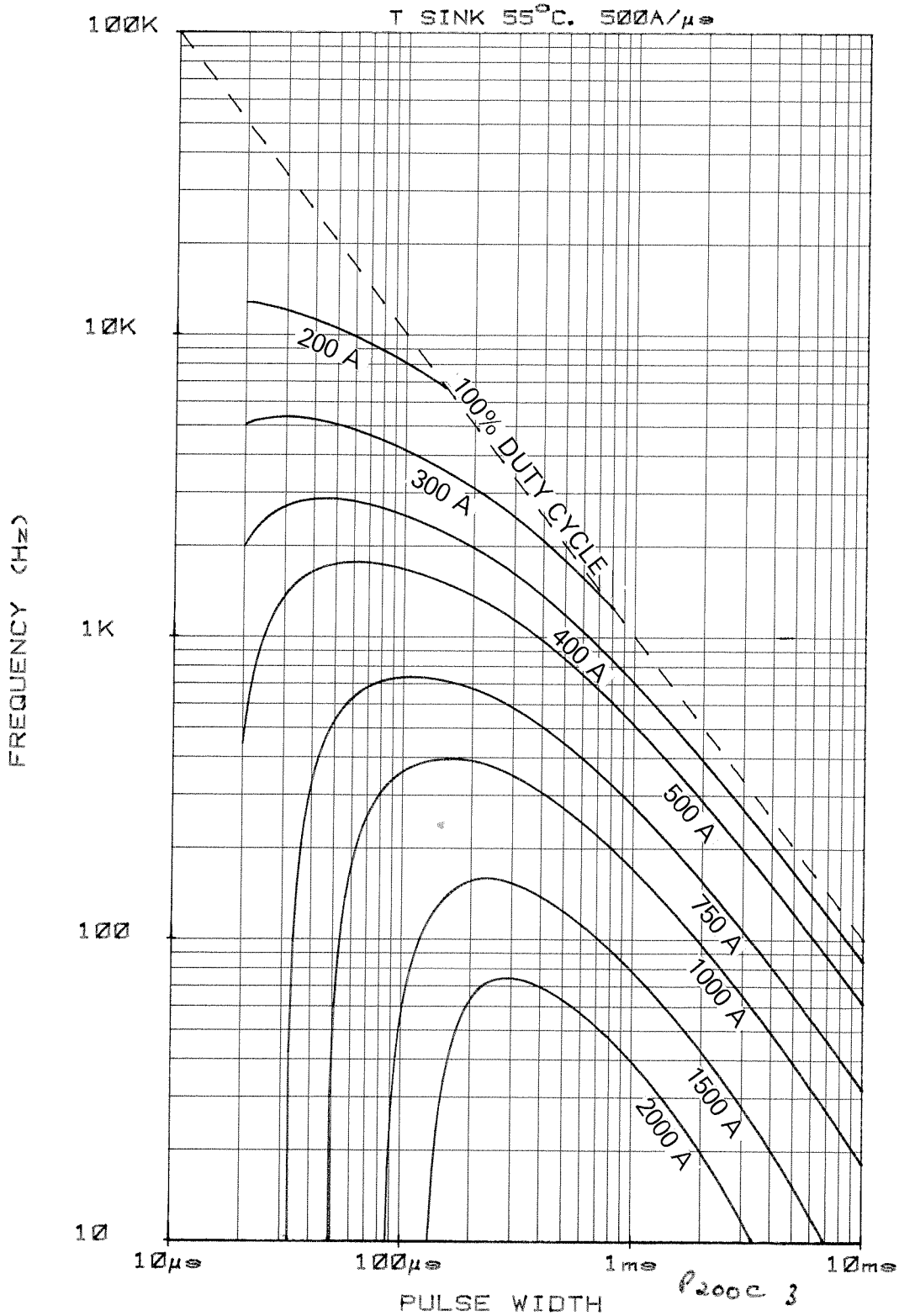
*NOTE: ENERGY PER PULSE SHOULD BE ADJUSTED PRO RATA WITH APPLIED PEAK RECOVERY VOLTAGE

P200C 11



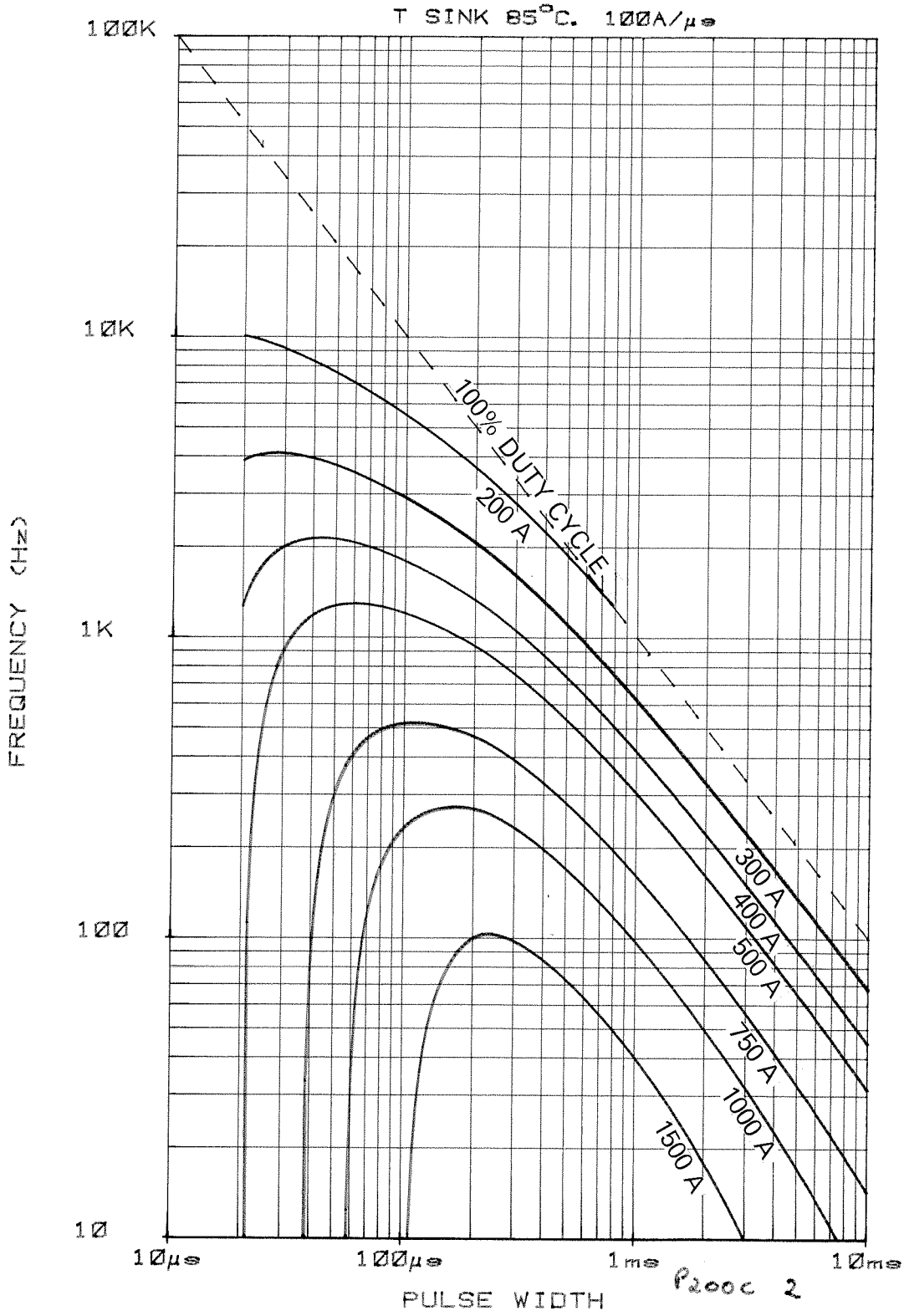
P200C 1

R200C 13

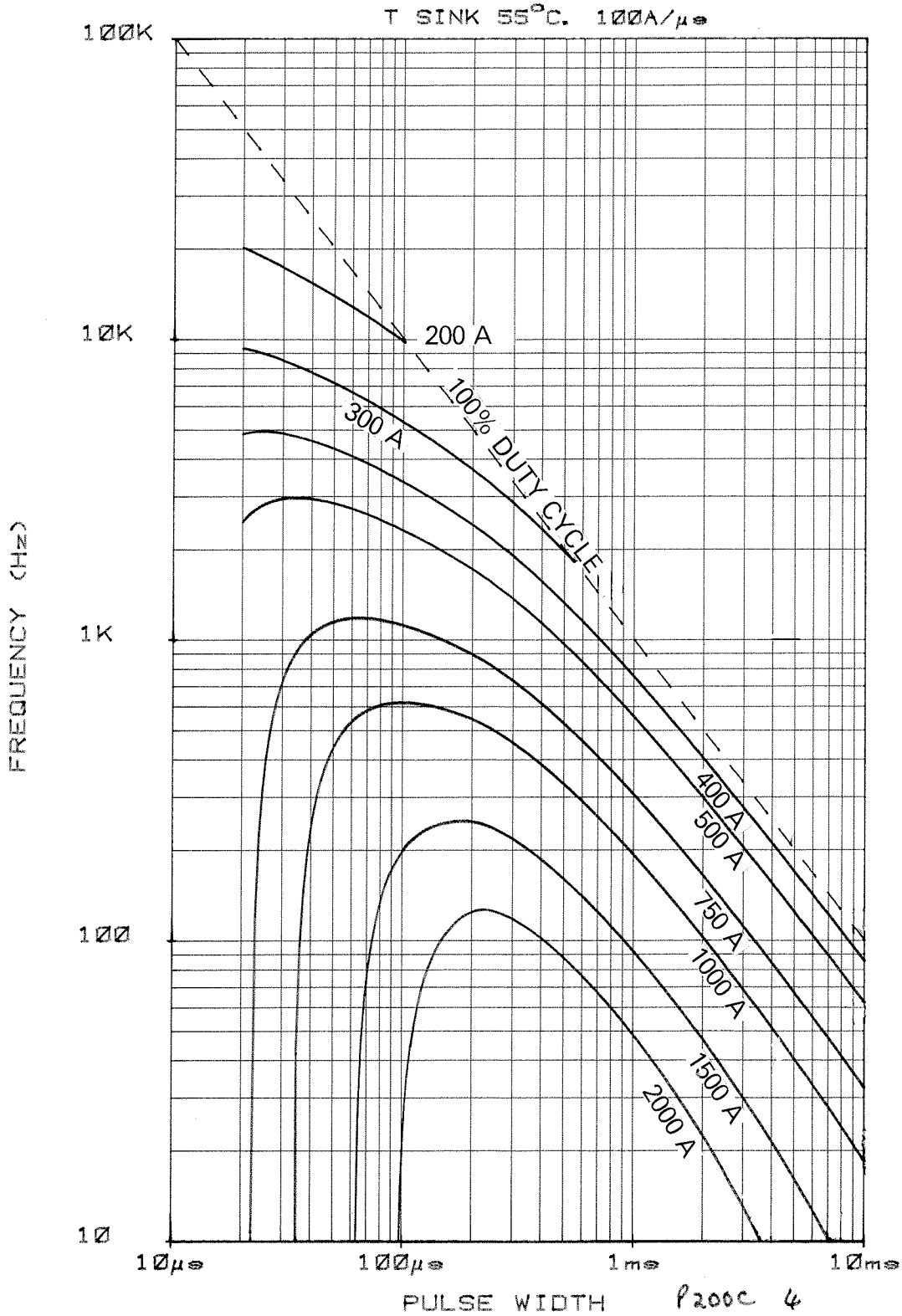


R200C 3

P200C'2

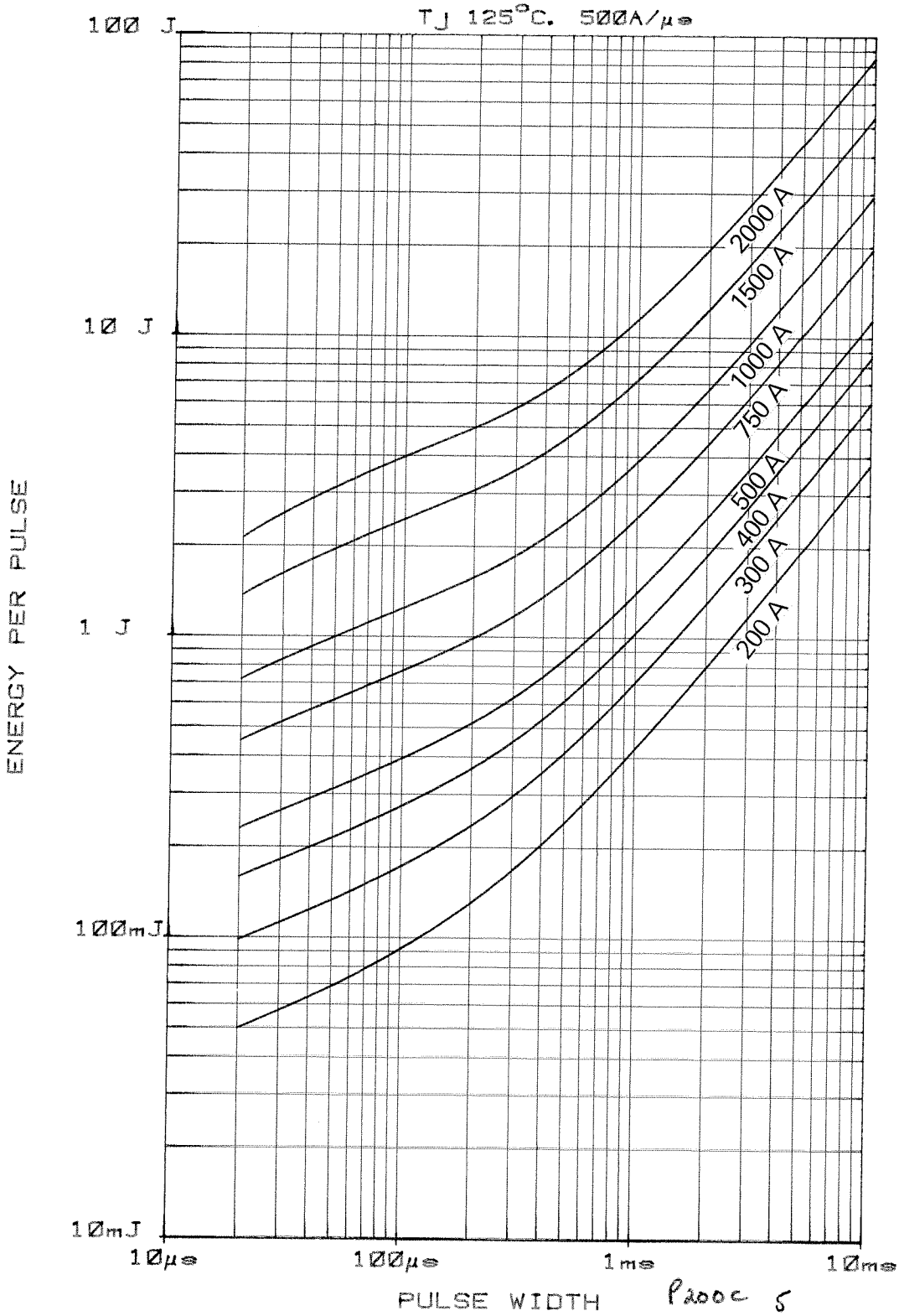

T SINK 85°C. 100A/µs
100K
10K
1K
100
10
FREQUENCY (Hz)
100% DUTY CYCLE
200 A
300 A
400 A
500 A
750 A
1000 A
1500 A
10µs
100µs
1ms
10ms
PULSE WIDTH
P200C 2

P200C/4



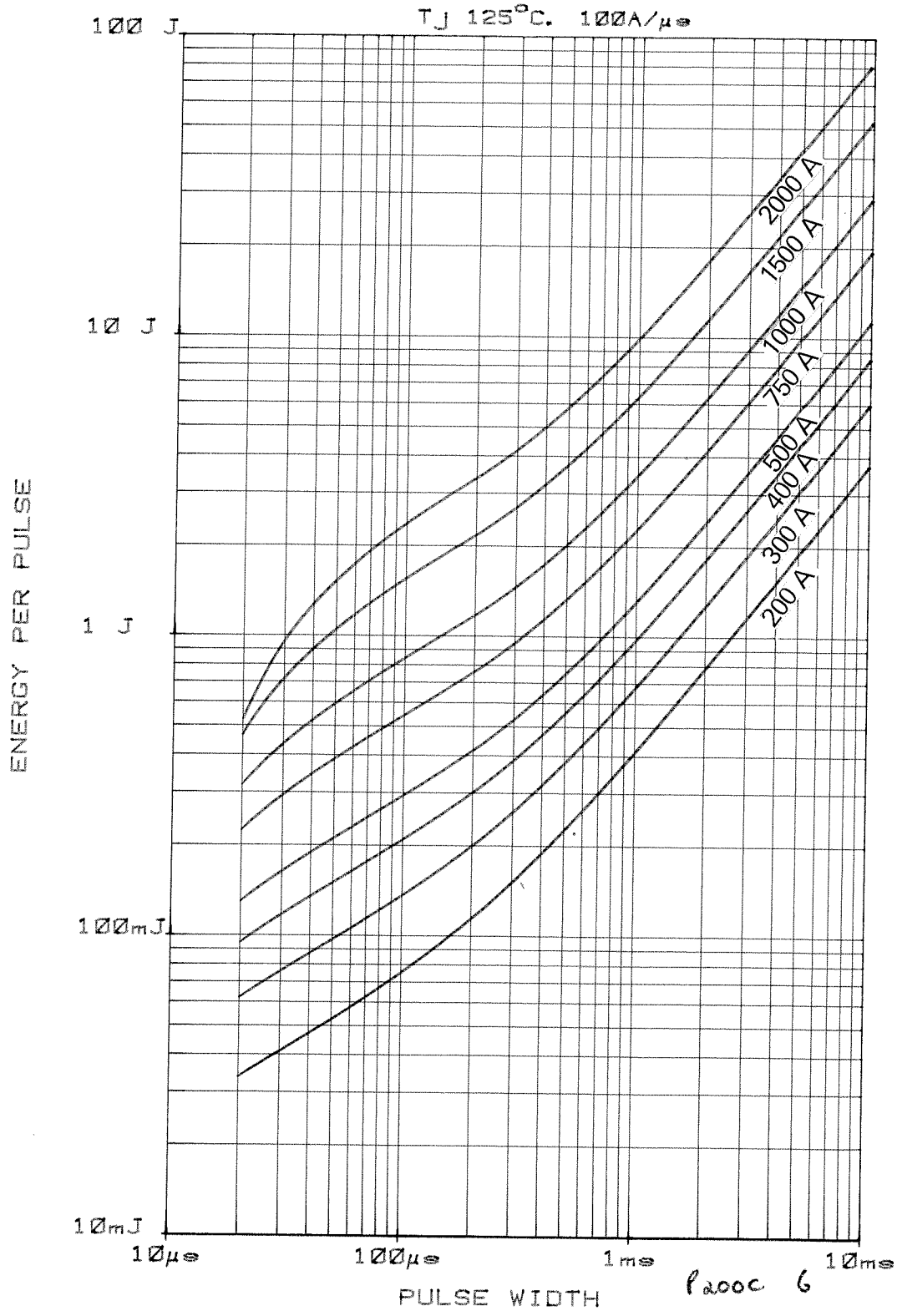
P200C 4

P200C/5



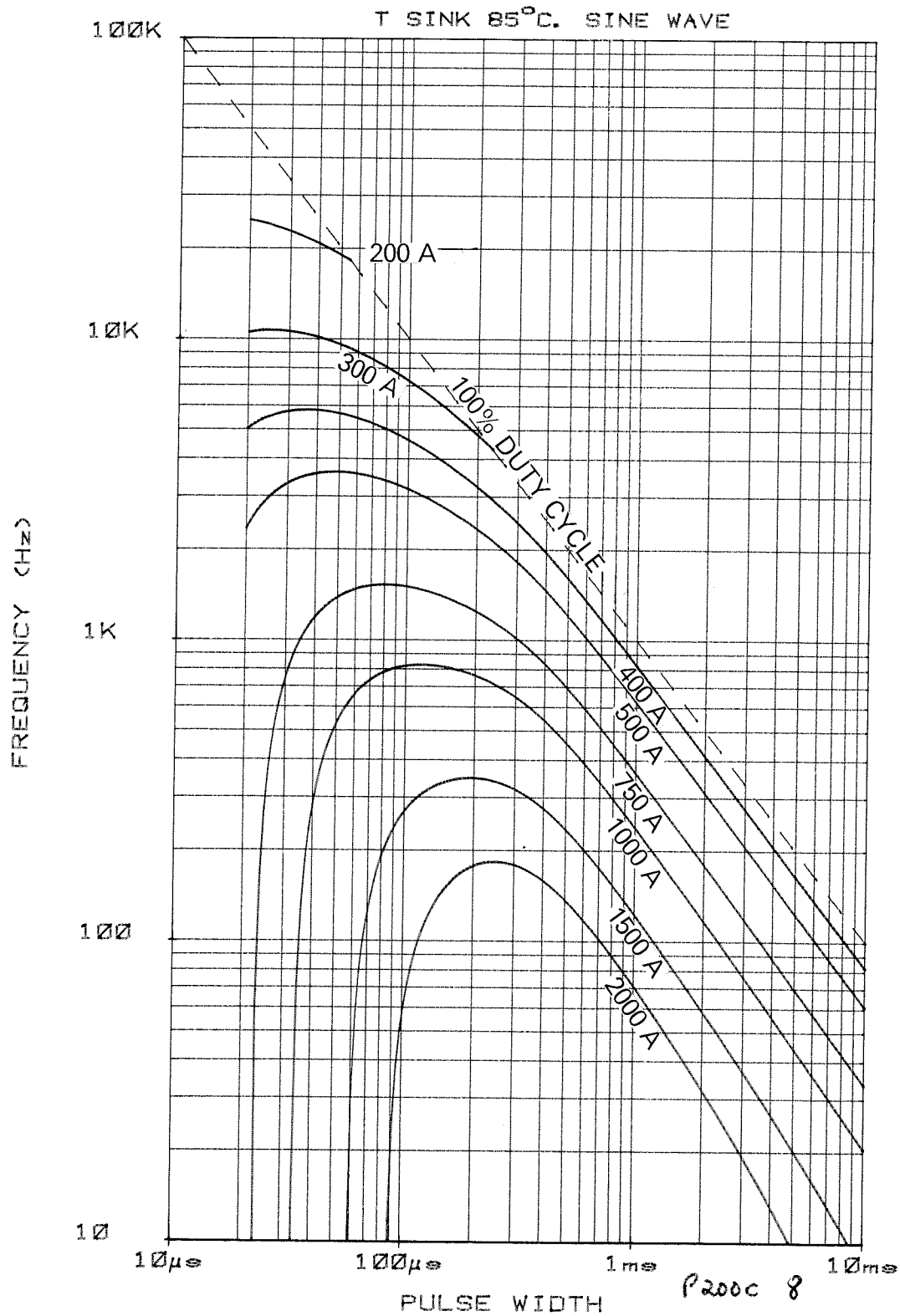
P200C 5

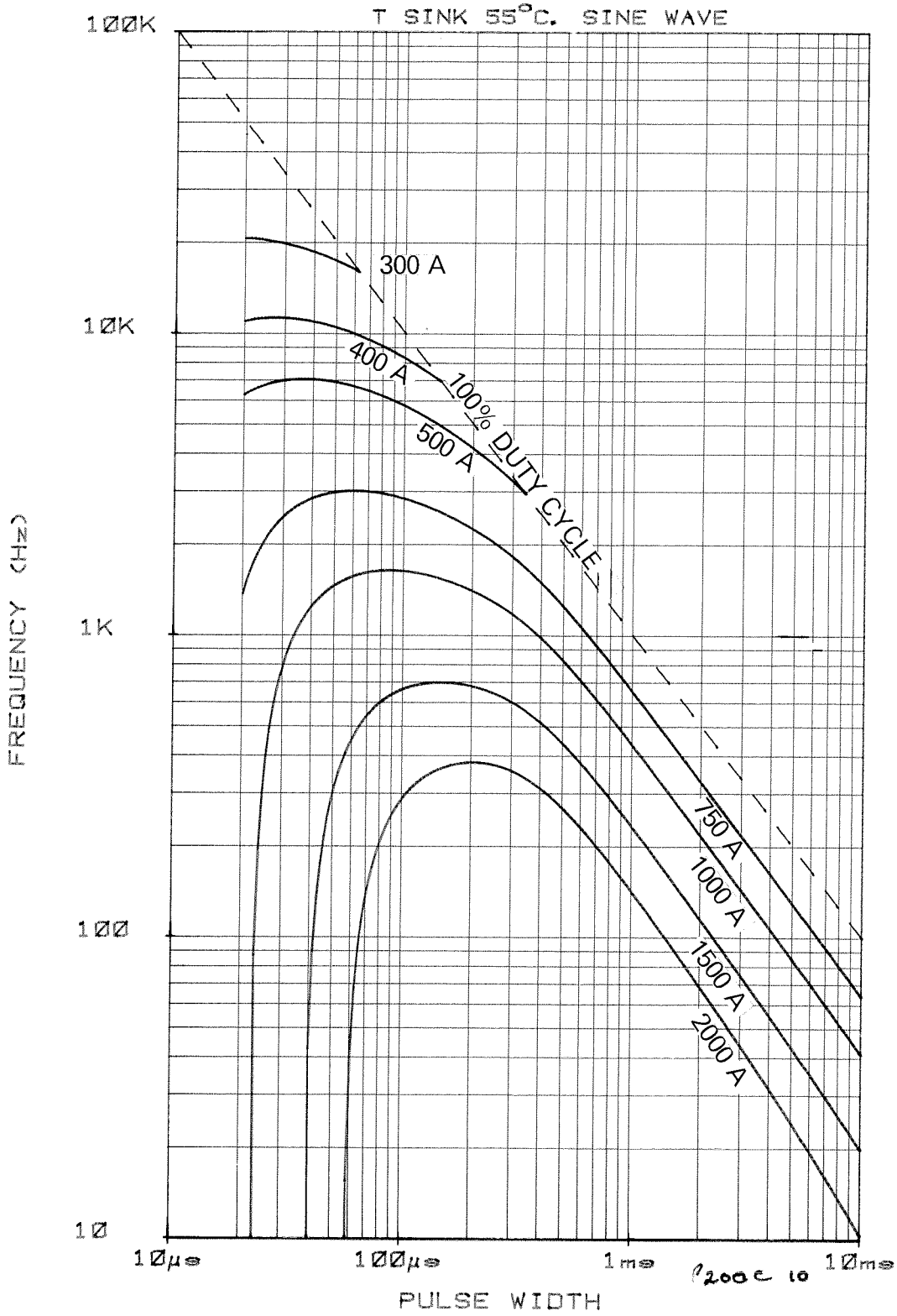
P200C 6

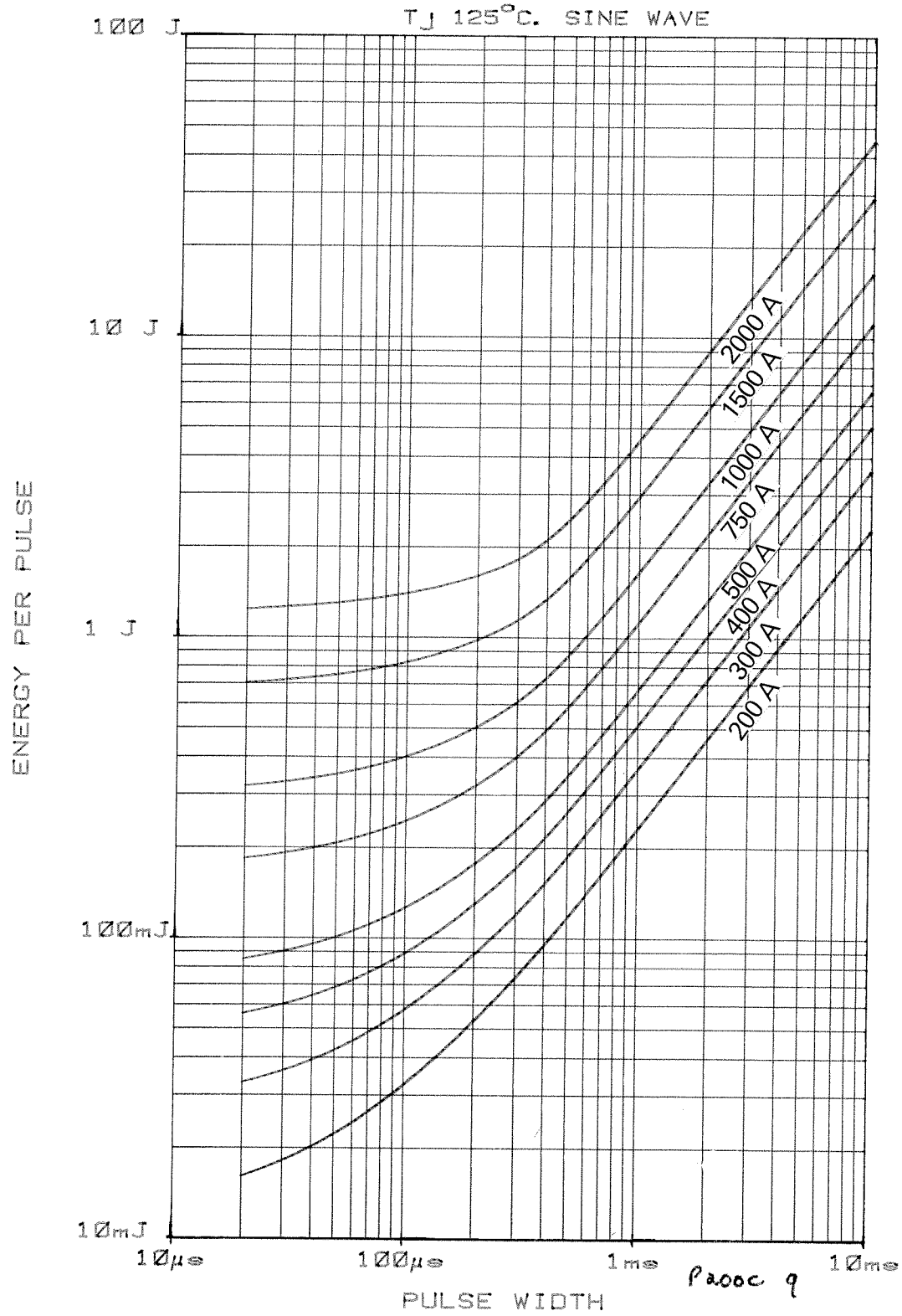


P200C 6

P200C'8


T SINK 85°C. SINE WAVE
100K
10K
1K
100
10
FREQUENCY (Hz)
200 A
300 A
100% DUTY CYCLE
400 A
500 A
750 A
1000 A
1500 A
2000 A
10µs
100µs
1ms
10ms
PULSE WIDTH
P200C 8


T SINK 55°C. SINE WAVE
100K
10K
1K
100
10
FREQUENCY (Hz)
300 A
400 A
500 A
100% DUTY CYCLE
750 A
1000 A
1500 A
2000 A
10µs
100µs
1ms
10ms
PULSE WIDTH


TJ 125°C. SINE WAVE
100 J
10 J
1 J
100mJ
10mJ
ENERGY PER PULSE
2000 A
1500 A
1000 A
750 A
500 A
400 A
300 A
200 A
10µs
100µs
1ms
10ms
PULSE WIDTH

SCALE	1/1
DRN	
CHKD	
APPD	
	~~GEC~~ 1
	CS 1
	QA 1
	LP 2
	HP 2
	6
S	NI

INTERNATIONAL OUTLINE No. TO-200AB

WEIGHT. 70 GRAMS.

FINISH. NICKEL PLATE. - 24 -

DEVICE MARKING INCLUDES MONOGRAM, TYPE No., SPEC. No. AND POLARITY SYMBOL.

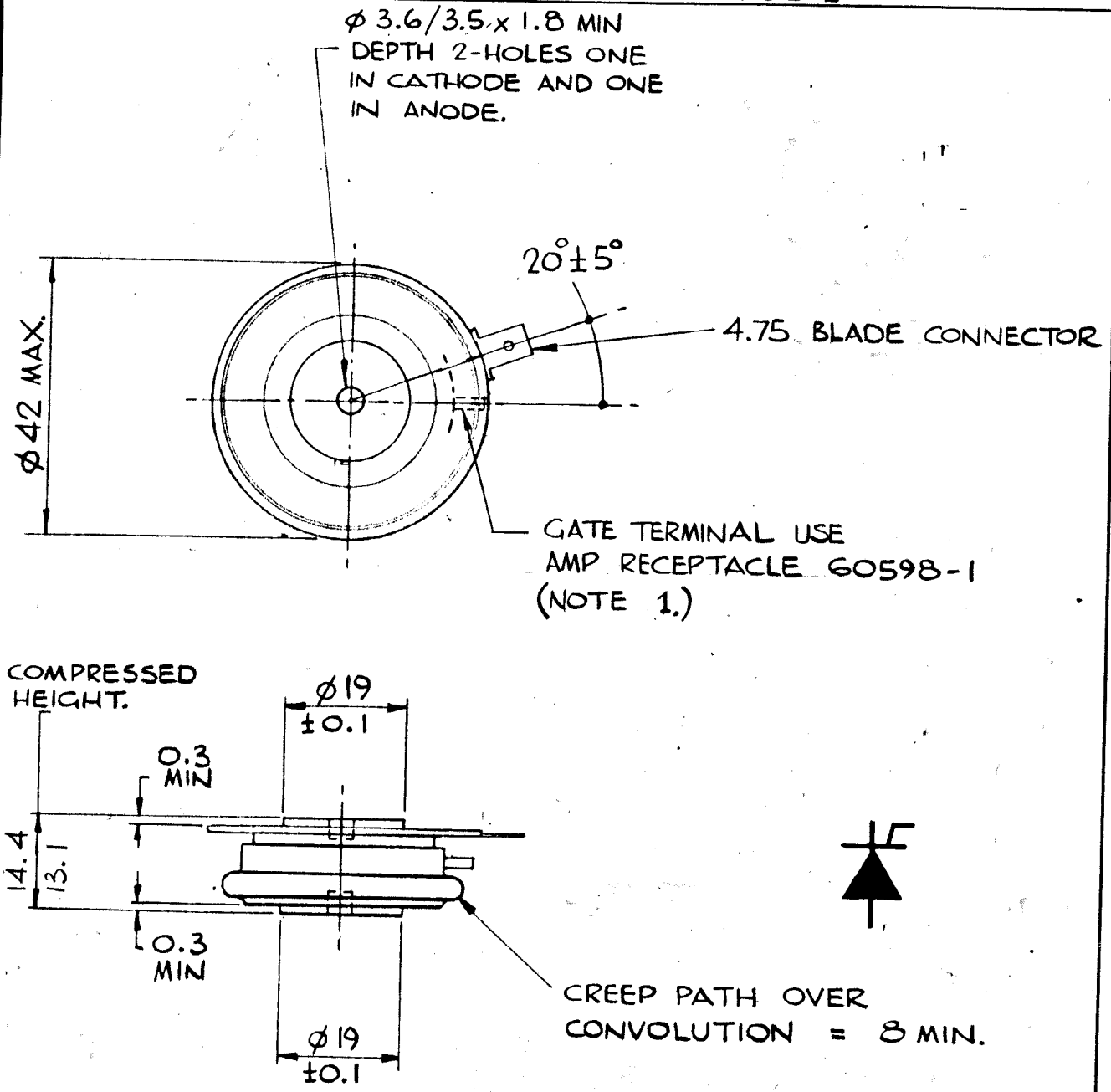
DEVICE MOUNTING: CLAMPING FORCE TO BE APPLIED ON ℄ OF LOCATION HOLES AND BE EVENLY DISTRIBUTED OVER AREA OF CONTACT. FLAT TOL ON SURFACES TO WHICH DEVICE IS CLAMPED TO BE 0.04 WIDE.

CLAMPING FORCE = 330 - 550 kgf.

NOTE 1. 300mm LONG GATE LEADS ARE AVAILABLE IF REQD.

G.A. DRG. No. 159B100H100-H110. 103B211. 103B212.

TYPE NUMBER		
N086C	P070C	P205C
N105C	P086C	P214C
N140C	P095C	P215C
N170C	P105C	P270C
N195C	P200C	
N275C	P202C	
	P204C	
	P100C	



WESTINGHOUSE BRAKE AND SIGNAL CO. LTD.
CHIPPENHAM, WILTSHIRE, SN15 1JD, ENGLAND.

WESTCODE ® SEMICONDUCTORS

THIRD ANGLE PROJECTION

DIMNS. IN MILLIMETRES

DRG. No. 101A212

ISS	REVISIONS
1	19.9.76 P118
2	P304 17.5.78 REDRAWN. ø19 WAS ø29. 0.3 ADDED. 15.2/14 WAS 15.2/12.5. LEADS ADDED.
3	M613 14.6.78 LEAD COLOURS CHANGED.
4	M636 7.8.78 LEADS DELETED
5	11.9.78 CLAMP FORCE WAS 500-1200 kgf. ø42 WAS ø43. NOTE 1 ADDED. 14.35/13.08 WAS 15.2/14.
6	19.9.78 14.4/13.1 WAS 14.35/13.08
7	30.10.78 M670 TYPE Nº ADDED
8	17.9.79 M773 550kgf WAS 700kgf.

5355E OZALID (U.K.) LTD

A4